

APPLICATIONS

- Snubber Diode For GTO Applications.

KEY PARAMETERS

V_{RRM}	4500V
$I_{F(AV)}$	430A
I_{FSM}	3500A
Q_r	440μC
t_{rr}	3.07μs

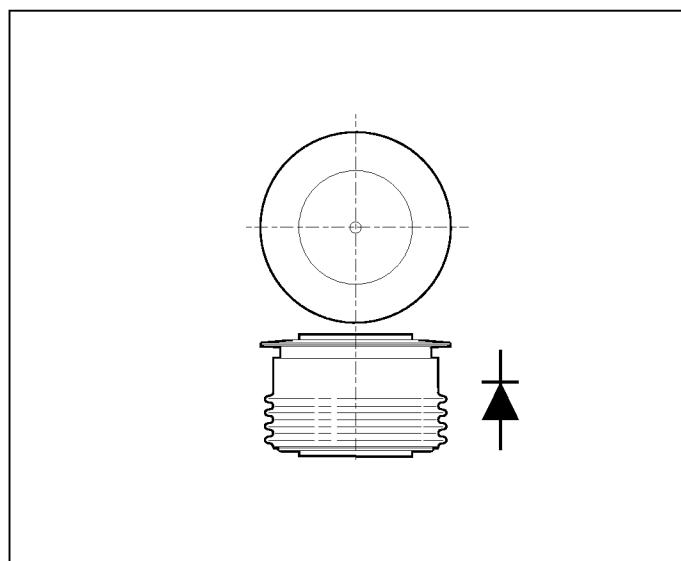
FEATURES

- Double side cooling.
- High surge capability.
- Low recovery charge.

VOLTAGE RATINGS

Type Number	Repetitive Peak Reverse Voltage V_{RRM}	Conditions
DSF8045SK45 DSF8045SK44 DSF8045SK43 DSF8045SK42 DSF8045SK41 DSF8045SK40	4500 4400 4300 4200 4100 4000	$V_{RSM} = V_{RRM} + 100V$

Lower voltage grades available.



Outline type code: K. See package outlines for further information.

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, $T_{case} = 65^{\circ}C$	430	A
$I_{F(RMS)}$	RMS value	$T_{case} = 65^{\circ}C$	680	A
I_F	Continuous (direct) forward current	$T_{case} = 65^{\circ}C$	600	A
Single Side Cooled (Anode side)				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, $T_{case} = 65^{\circ}C$	285	A
$I_{F(RMS)}$	RMS value	$T_{case} = 65^{\circ}C$	445	A
I_F	Continuous (direct) forward current	$T_{case} = 65^{\circ}C$	380	A

DSF8045SK

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; with 0% V_{RRM} , $T_j = 150^{\circ}C$	3.5	kA
I^2t	I^2t for fusing		61.25×10^3	A ² s
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; with 50% V_{RRM} , $T_j = 150^{\circ}C$	2.8	kA
I^2t	I^2t for fusing		39.2×10^3	A ² s

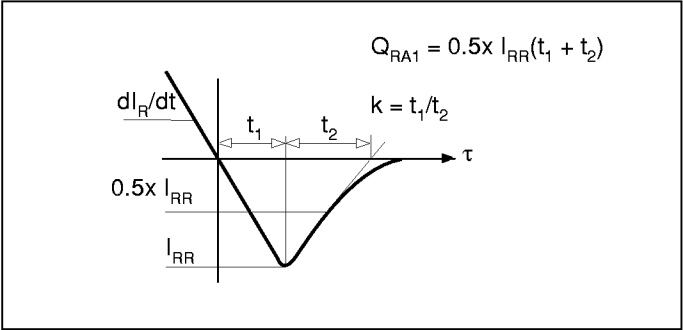
THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.048	°C/W
		Single side cooled	Anode dc	-	0.09	°C/W
			Cathode dc	-	0.103	°C/W
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Clamping force 8.0kN with mounting compound	Double side	-	0.01	°C/W
			Single side	-	0.02	°C/W
T_{vj}	Virtual junction temperature	Forward (conducting)		-	150	°C
T_{stg}	Storage temperature range			-55	175	°C
-	Clamping force			7.0	9.0	kN

CHARACTERISTICS

Symbol	Parameter	Conditions	Typ.	Max.	Units
V_{FM}	Forward voltage	At 1000A peak, $T_{case} = 25^{\circ}C$	-	4.0	V
I_{RRM}	Peak reverse current	At V_{RRM} , $T_{case} = 150^{\circ}C$	-	50	mA
t_{rr}	Reverse recovery time	$I_F = 1000A$, $di_{RR}/dt = 100A/\mu s$ $T_{case} = 150^{\circ}C$, $V_R = 100V$	-	3.07	μs
Q_{RA1}	Recovered charge (50% chord)		-	440	μC
I_{RM}	Reverse recovery current		-	240	A
K	Soft factor		-	-	-
V_{TO}	Threshold voltage	At $T_{vj} = 150^{\circ}C$	-	1.7	V
r_T	Slope resistance	At $T_{vj} = 150^{\circ}C$	-	2.1	$m\Omega$
V_{FRM}	Forward recovery voltage	$di/dt = 1000A/\mu s$, $T_j = 125^{\circ}C$	-	300	V

DEFINITION OF K FACTOR AND Q_{RA1}



CURVES

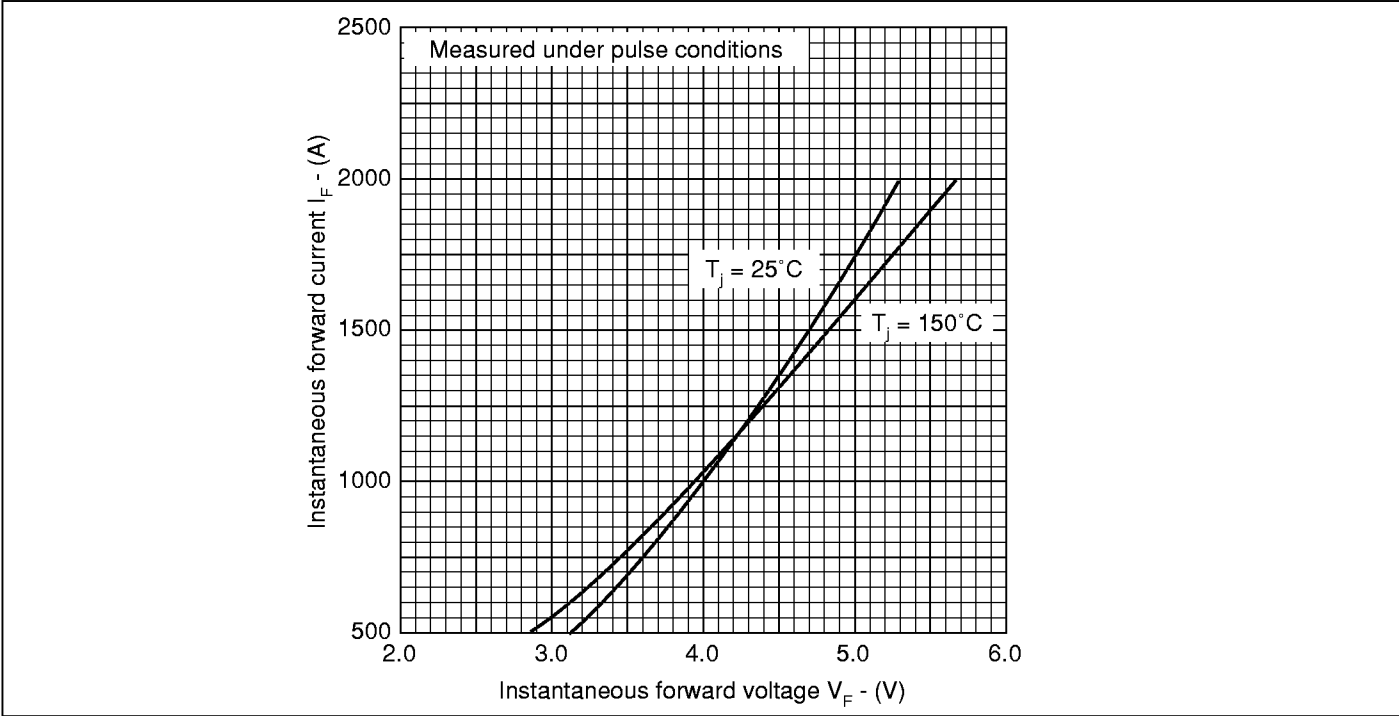


Fig.1 Maximum (limit) forward characteristics

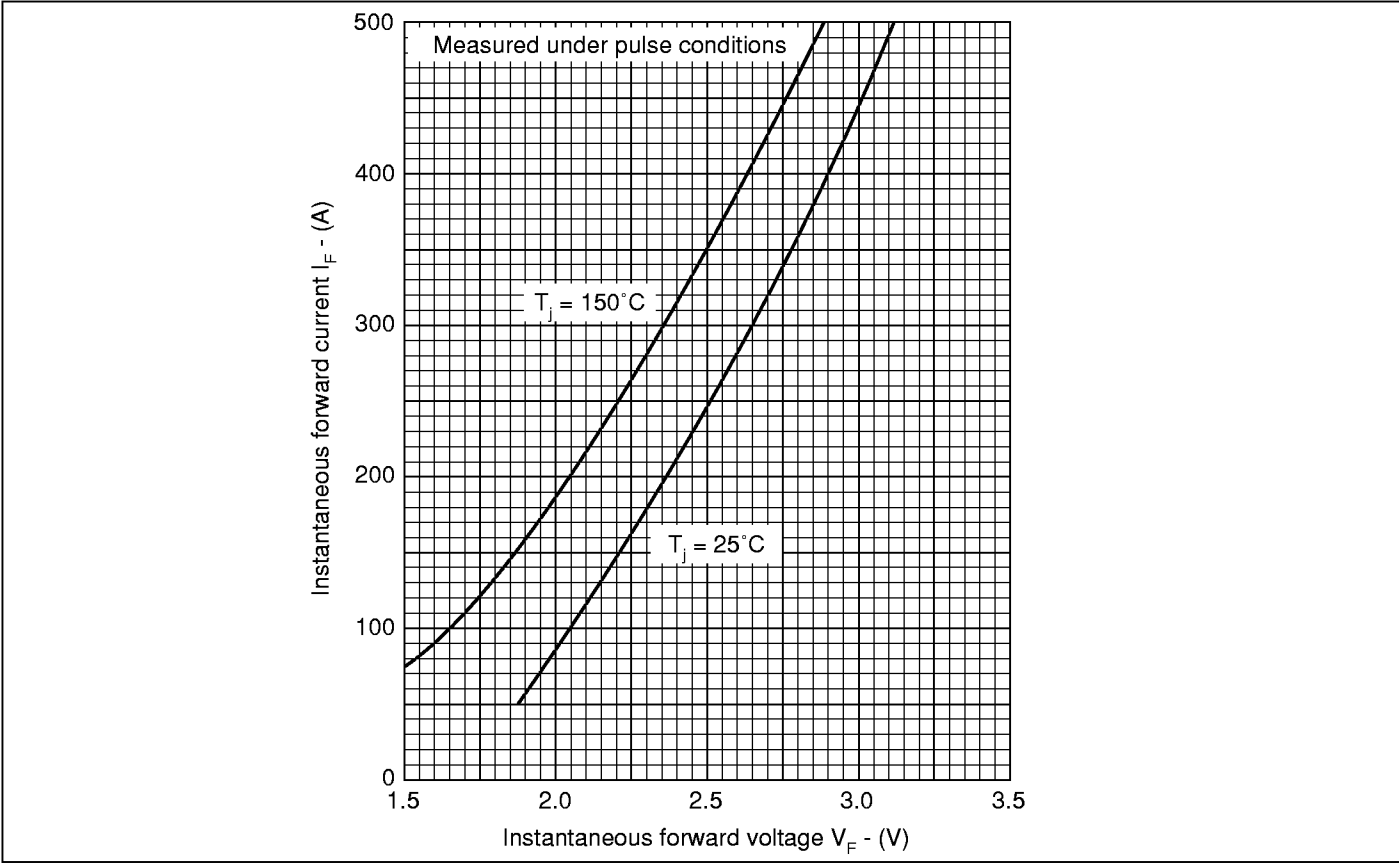


Fig.2 Maximum (limit) forward characteristics

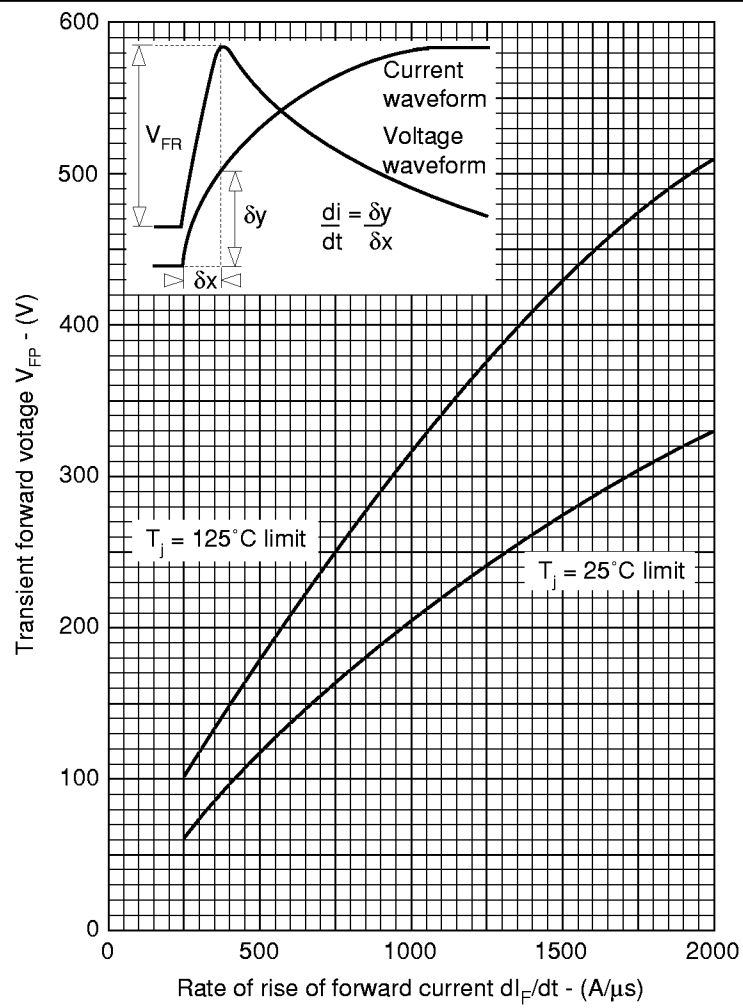


Fig.3 Transient forward voltage vs rate of rise of forward current

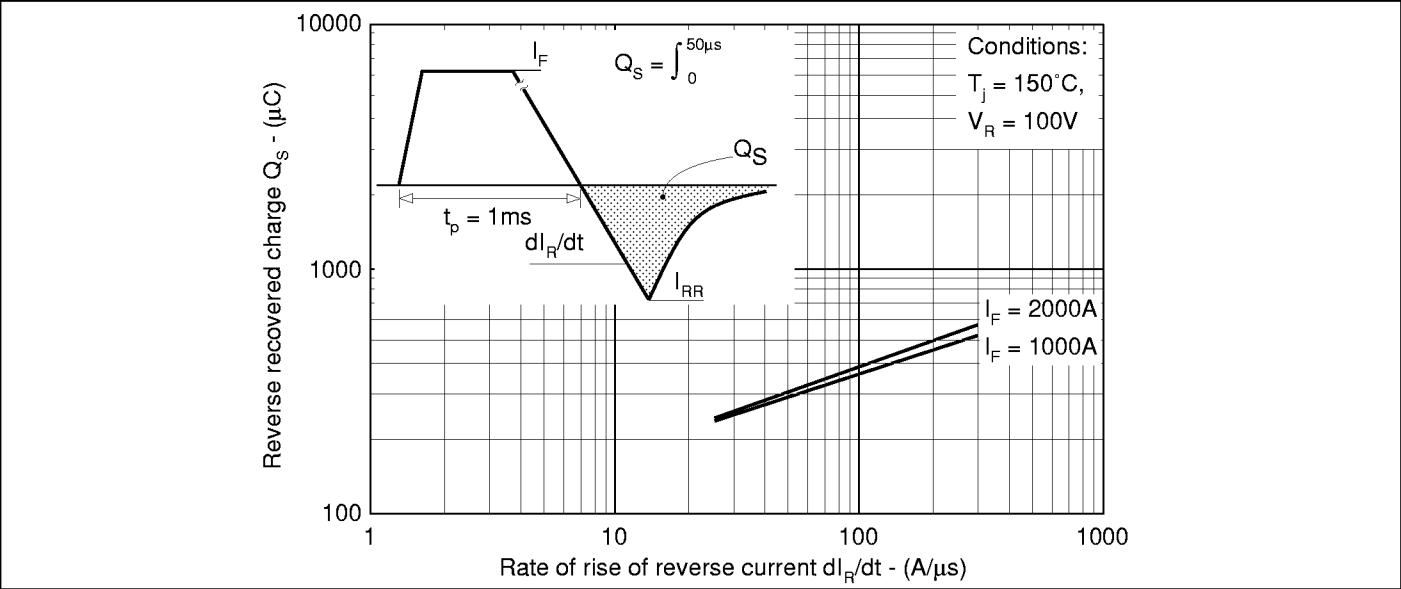


Fig. 4 Typical recovered charge

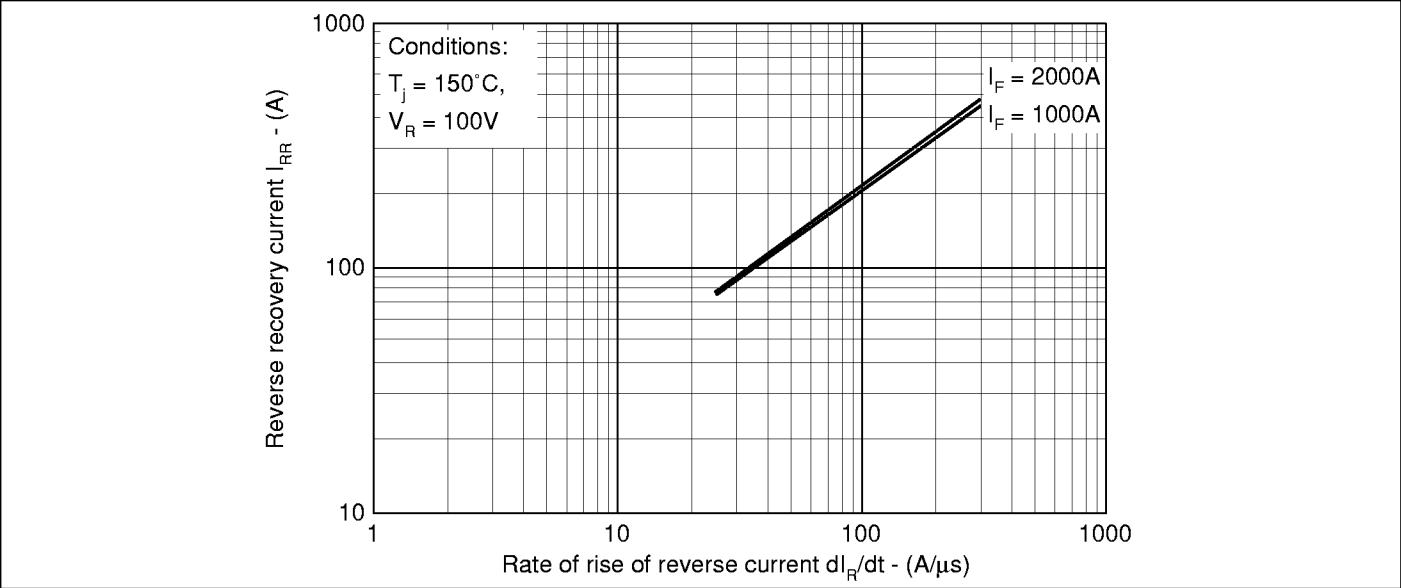


Fig. 5 Typical reverse recovery current vs rate of rise of reverse current

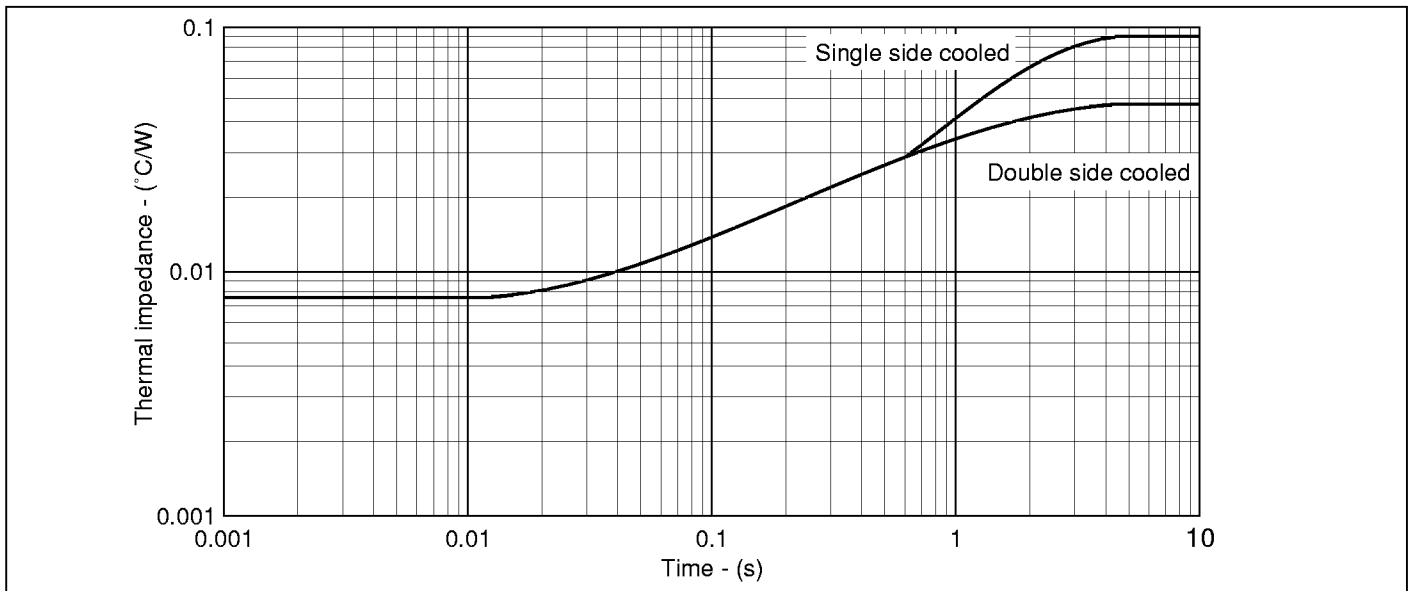
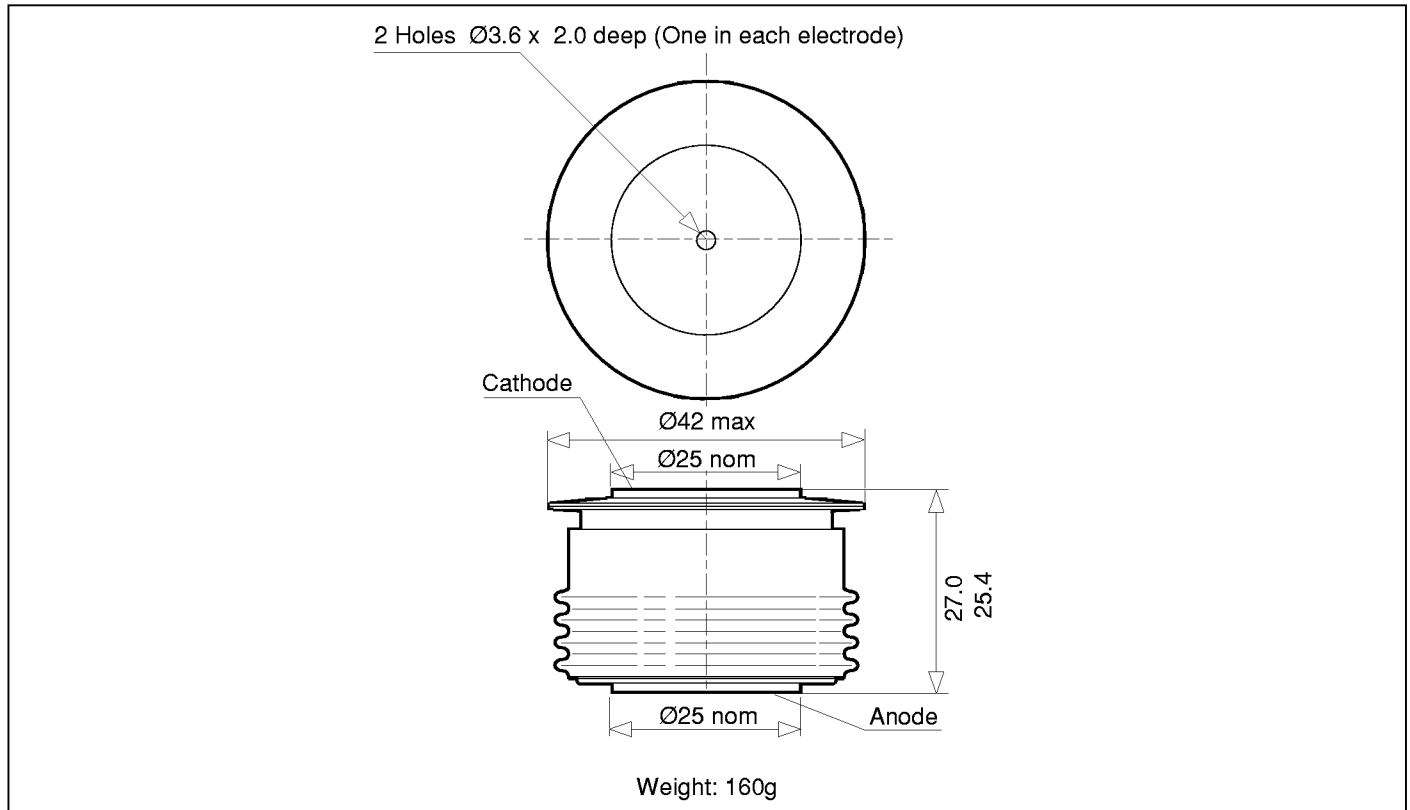


Fig.6 Maximum (limit) transient thermal impedance - junction to case - ($^{\circ}\text{C/W}$)

PACKAGE DETAILS - K

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



HEADQUARTERS OPERATIONS
MITEL SEMICONDUCTOR
Cheney Manor, Swindon,
Wiltshire SN2 2QW, United Kingdom.
Tel: (01793) 518000
Fax: (01793) 518411

MITEL SEMICONDUCTOR
1500 Green Hills Road,
Scotts Valley, California 95066-4922
United States of America.
Tel (408) 438 2900
Fax: (408) 438 5576/6231

Internet: <http://www.gpsemi.com>

POWER PRODUCT CUSTOMER SERVICE CENTRES

- **FRANCE, BENELUX & SPAIN** Les Ulis Cedex Tel: (1) 69 18 90 00 Fax : (1) 64 46 54 50
- **GERMANY** Munich Tel: (089) 419508-20 Fax : (089) 419508-55
- **NORTH AMERICA** Dedham, USA Tel: (781) 251 0126 Fax: (781) 251 0106
- **UK** Lincoln Tel: (01522) 500500 Fax : (01522) 510550

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